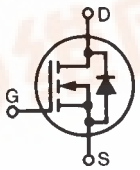
IXYS

PolarHV™ Power MOSFET

IXTP 2N60P
IXTY 2N60P

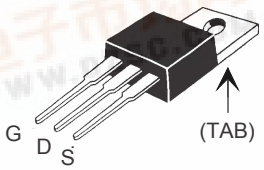
V_{DSS} = 500 V
I_{D25} = 2 A
$R_{DS(on)}$ ≤ 5.1 Ω

N-Channel Enhancement Mode
Avalanche Rated

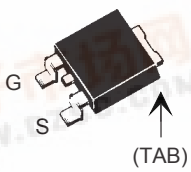


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25° C to 150° C	600	V
V_{DGR}	T_J = 25° C to 150° C; R_{GS} = 1 MΩ	600	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	T_C = 25° C	2	A
I_{DM}	T_C = 25° C, pulse width limited by T_{JM}	4	A
I_{AR}	T_C = 25° C	2	A
E_{AR}	T_C = 25° C	10	mJ
E_{AS}	T_C = 25° C	150	mJ
dv/dt	$I_S \le I_{DM}$, di/dt ≤100 A/µs, $V_{DD} \le V_{DSS}$, T_J ≤150° C, R_G = 50 Ω	10	V/ns
P_D	T_C = 25° C	55	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	1.6 mm (0.062 in.) from case for 10 s	300	°C
T_{SOLD}	Plastic body for 10 s	260	°C
M_d	Mounting torque (TO-220)	1.13/10	Nm/lb.in.
Weight	TO-220	4	g
	TO-252	0.8	g

TO-220 (IXTP)



TO-252 AA (IXTY)



G = Gate D = Drain
S = Source TAB = Drain

Symbol (T_J = 25° C, unless otherwise specified)	Test Conditions	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0 V, I_D = 25 µA	600			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 250 µA	3.0		5.0	V
I_{GSS}	V_{GS} = ±30 V, V_{DS} = 0 V			±50	nA
I_{DSS}	$V_{DS} = V_{DSS}$, V_{GS} = 0 V			1	µA
	T_J = 125° C			50	µA
$R_{DS(on)}$	V_{GS} = 10 V, $I_D = 0.5\ I_{D25}$ Pulse test, t ≤300 µs, duty cycle d ≤ 2 %			5.1	Ω

Features

- International standard packages
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
  - easy to drive and to protect

Advantages

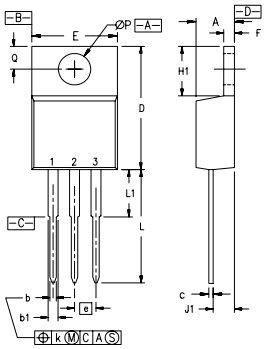
- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions (T_J = 25° C, unless otherwise specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	V_{DS}= 20 V; I_D = 0.5 I_{D25}, pulse test	1.4	2.2		S
C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		240		pF
C_{oss}			28		pF
C_{rss}			3.5		pF
$t_{d(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D =0.5 I_{D25} R_G = 50 Ω (External)		28		ns
t_r			20		ns
$t_{d(off)}$			60		ns
t_f			23		ns
$Q_{g(on)}$	V_{GS}= 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}		7.0		nC
Q_{gs}			2.5		nC
Q_{gd}			2.1		nC
R_{thJC}				2.25	°C/W
R_{thCS}	(TO-220)		0.25		°C/W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25° C unless otherwise specified)	Characteristic Values Min.	Typ.	Max.	
I_S	V_{GS} = 0 V			2	A
I_{SM}	Repetitive			6	A
V_{SD}	I_F = I_S, V_{GS} = 0 V, Pulse test, t ≤300 µs, duty cycle d≤ 2 %			1.5	V
t_{rr}	I_F = 2 A -di/dt = 100 A/µs		400		ns

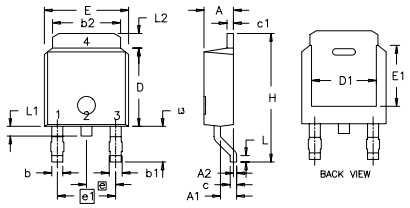
TO-220 (IXTP) Outline



Pins: 1 - Gate 2 - Drain
3 - Source 4 - Drain

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

TO-252 AA (IXTY) Outline



Pins: 1 - Gate 3 - Source
4 - Drain

Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	2.19	2.38	0.086	0.094
A1	0.89	1.14	0.035	0.045
A2	0	0.13	0	0.005
b	0.64	0.89	0.025	0.035
b1	0.76	1.14	0.030	0.045
b2	5.21	5.46	0.205	0.215
c	0.46	0.58	0.018	0.023
c1	0.46	0.58	0.018	0.023
D	5.97	6.22	0.235	0.245
D1	4.32	5.21	0.170	0.205
E	6.35	6.73	0.250	0.265
E1	4.32	5.21	0.170	0.205
e	2.28 BSC		0.090 BSC	
e1	4.57 BSC		0.180 BSC	
H	9.40	10.42	0.370	0.410
L	0.51	1.02	0.020	0.040
L1	0.64	1.02	0.025	0.040
L2	0.89	1.27	0.035	0.050
L3	2.54	2.92	0.100	0.115

Fig. 1. Output Characteristics @ 25°C

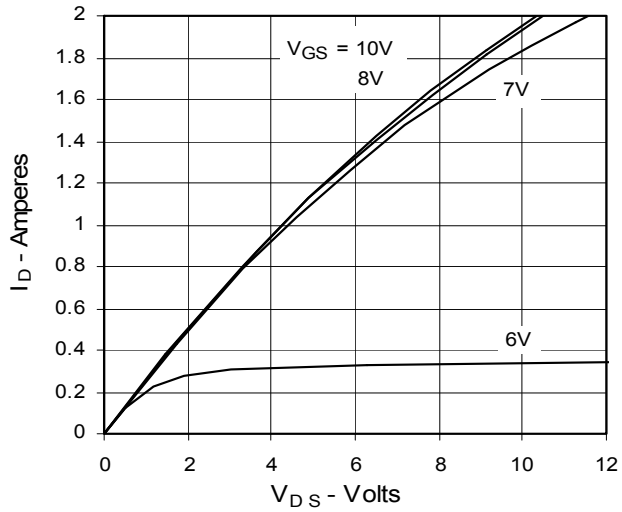


Fig. 2. Extended Output Characteristics @ 25°C

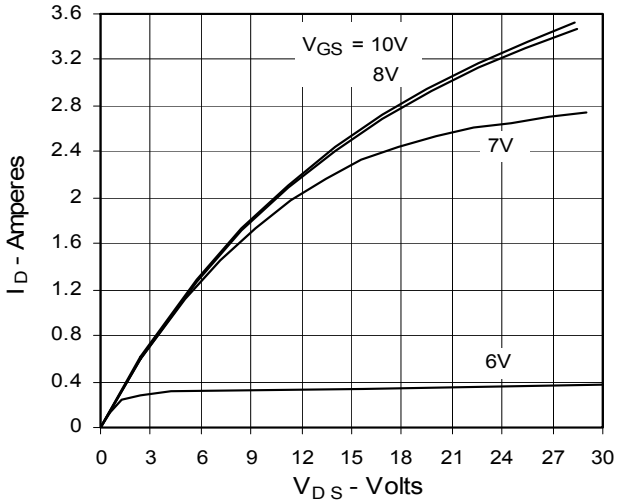


Fig. 3. Output Characteristics @ 125°C

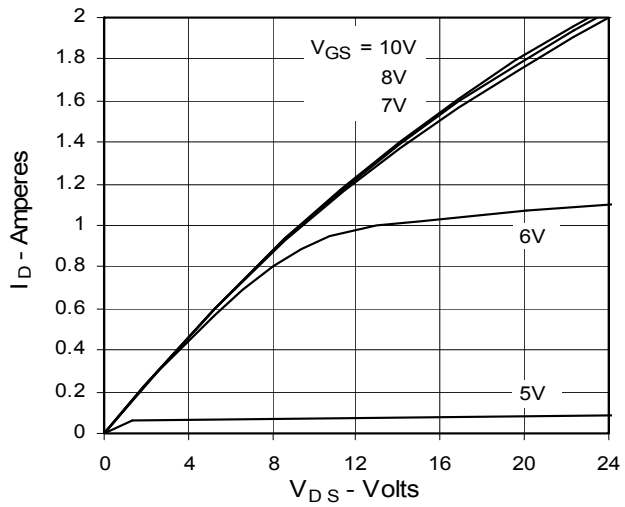


Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. Junction Temperature

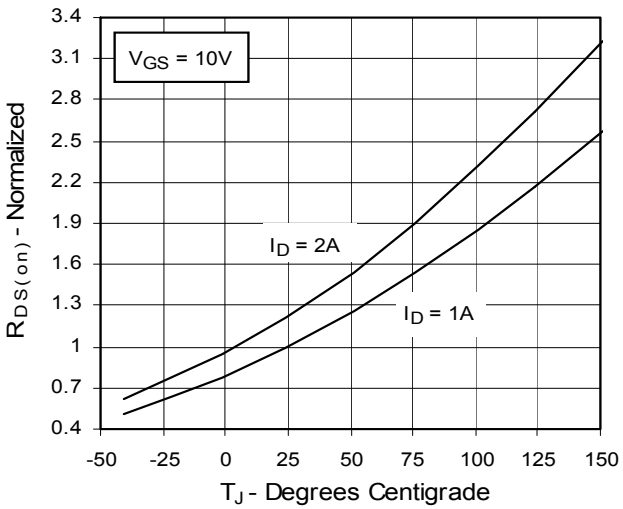


Fig. 5. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. I_D

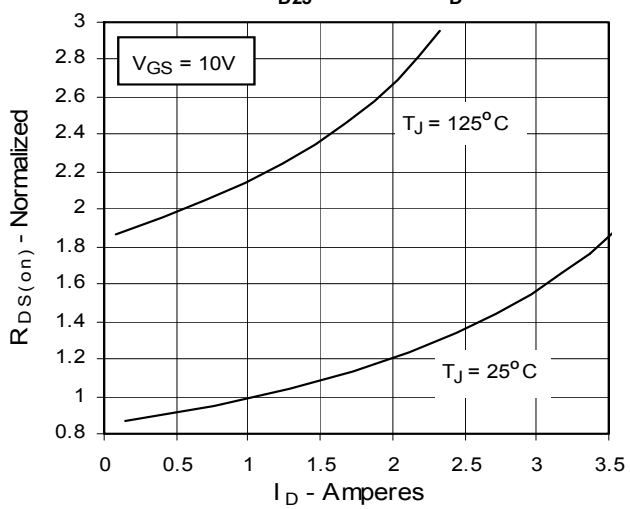


Fig. 6. Drain Current vs. Case Temperature

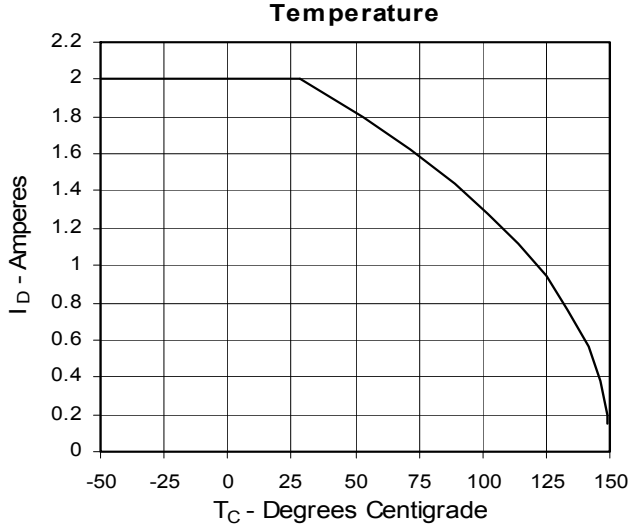


Fig. 7. Input Admittance

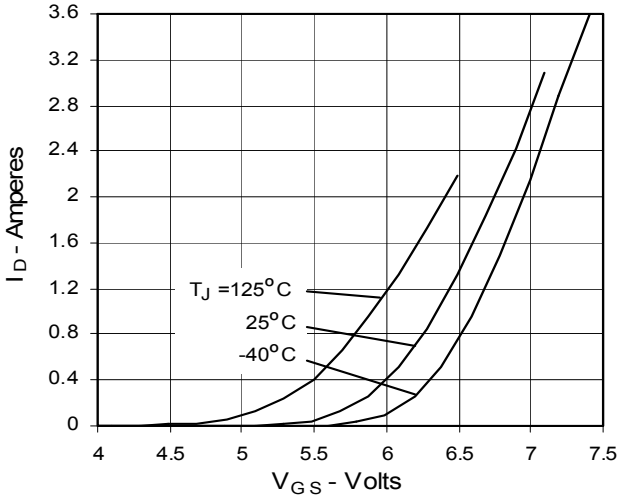


Fig. 8. Transconductance

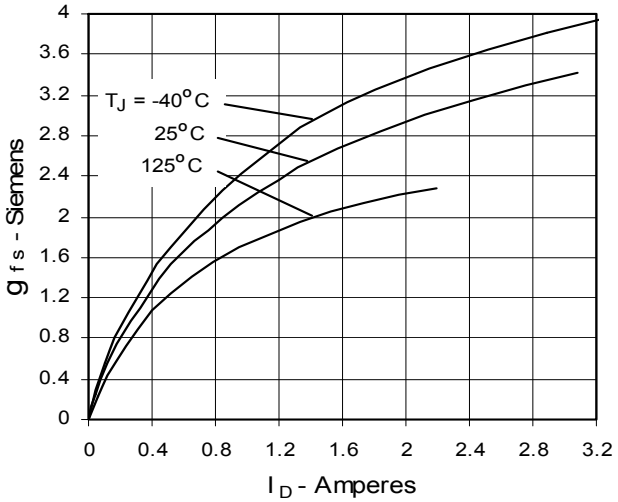


Fig. 9. Source Current vs. Source-To-Drain Voltage

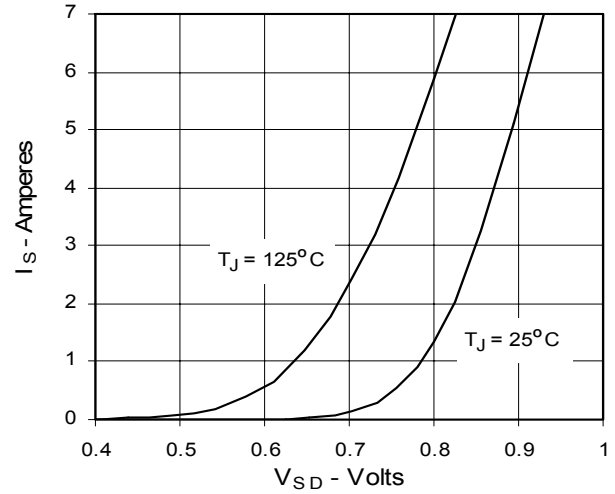


Fig. 10. Gate Charge

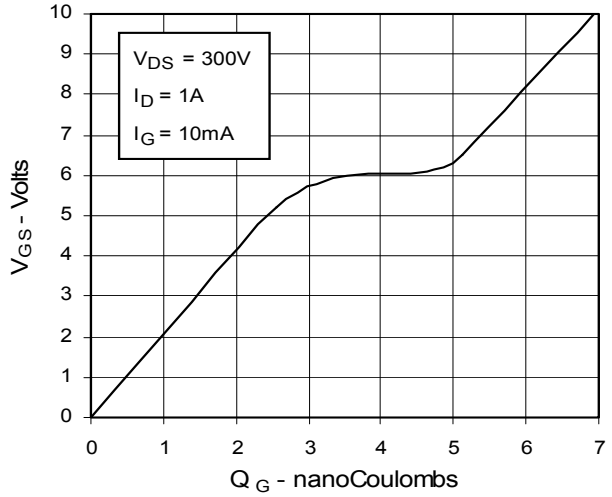


Fig. 11. Capacitance

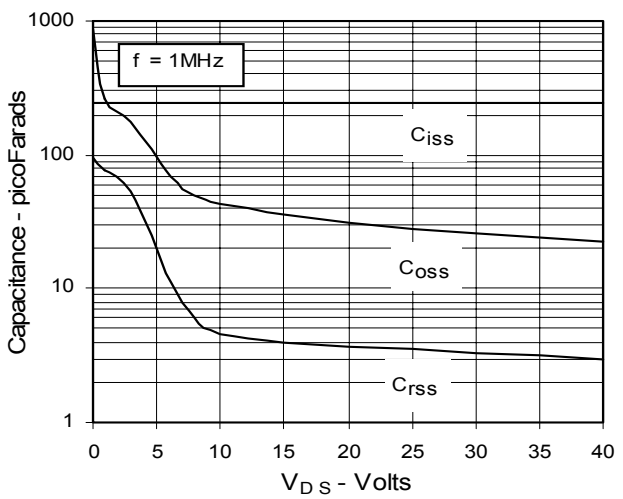


Fig. 13. Maximum Transient Thermal Resistance